## A simulation study for designed triple GEM detector at IOP

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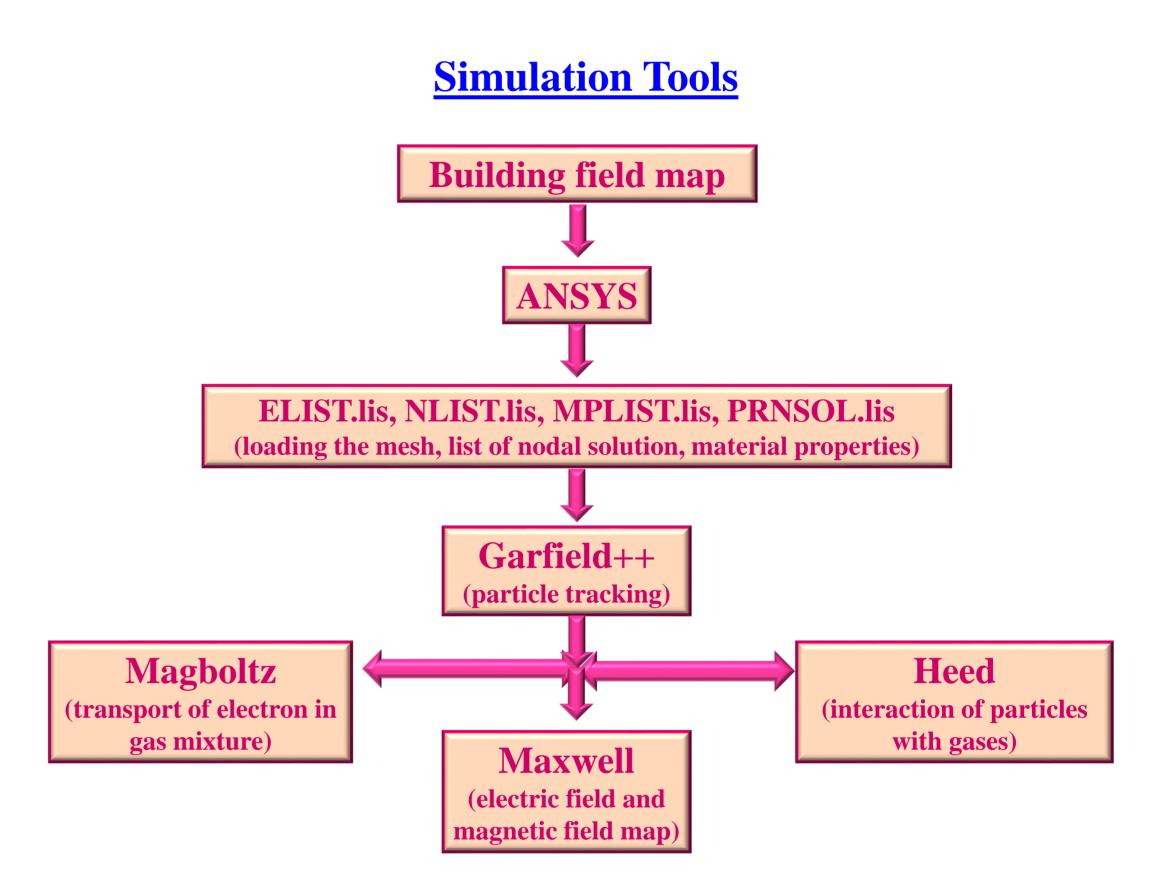
**Advanced Detectors for Nuclear, High Energy and Astroparticle Physics, Bose Institute, Kolkata-700004, India** 

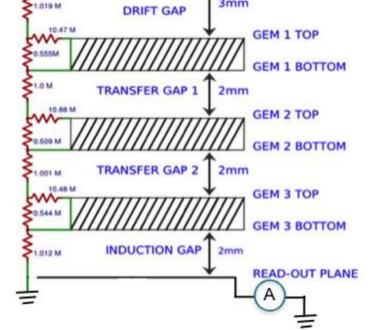
## Introduction

The GEM is one of the Micro Pattern Gas Detector (MPGD) proposed to be used as a readout for ALICE TPC upgrade in LHC experiment, at CERN [1]. The existing Multiple Wire Proportional Chamber (MWPC) will be replaced by GEM based readout which provides intrinsic ion blocking capability without any gating grid system [2]. At IOP detector laboratory, we have build a  $10 \text{ cm} \times 10$ cm standard triple GEM based detector prototype and tested it with  $Ar/CO_270/30$  gas mixture.

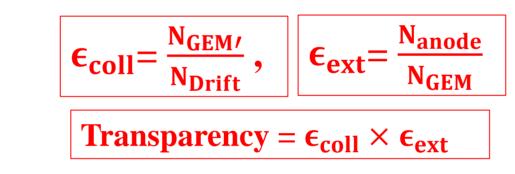
In order to study the properties of the detector, a full and detailed simulation have been performed with Garfield++ simulation package [3]. ANSYS is used to create the geometry of the detector and the meshing needed for the field calculations [4].







## **Numerical calculations and analysis**

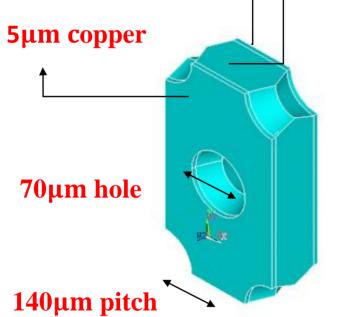


For triple gem setup

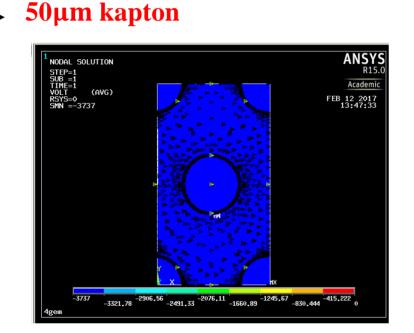
N<sub>GEM</sub><sup>'</sup> = No. of electrons getting inside the GEM hole N<sub>Drift</sub> = No. of electrons created above the GEM hole N<sub>GEM</sub> = No. of electrons created inside the GEM hole N<sub>anode</sub> = No. of electrons reaching anode plane



- **Drift : Transfer : Induction = 3 mm: 2 mm: 2 mm**
- Hexagonal geometry
- Pitch 140µm (SP)
- $Ar/CO_2: 70/30$ Ο
- Penning ratio r<sub>p</sub> : 0.57
- Voltage range Ο 3000 kV- 4600 kV



**Building field map** 

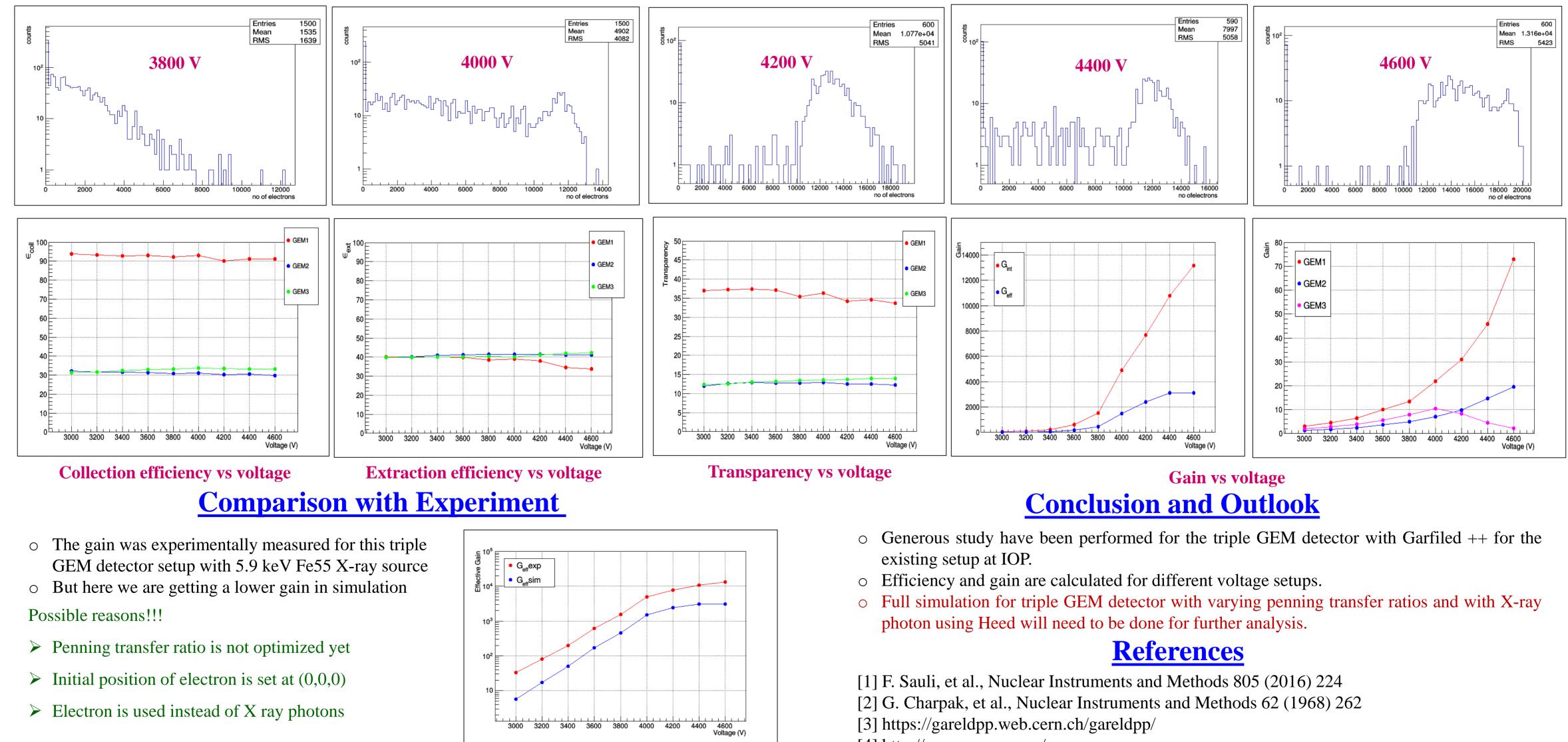


**Field mapping with ANSYS** 



**Results** 

**G**<sub>int</sub>= **Intrinsic gain** (mean no of e produced) **G**<sub>eff</sub> = Effective gain



[4] http://www.ansys.com/